Preface

The 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016) was held at Porto Carras Resort, Halkidiki, Greece. The Conference involved 274 abstracts including 15 plenary and invited talks as well as 3 invited posters. The conference provided a scientific forum for 480 participants from 26 countries.

ECSCRM is a biannual conference, which interleaves with the biannual International Conference on Silicon Carbide and Related Materials (ICSCRM). ECSCRM started at Heraklion, Crete, Greece, in 1996. The idea to organize a European conference on silicon carbide was born during discussions between partners of TECSICA, the first SiC related project funded by European Commission. Two of them (University of Montpellier II and Foundation for Research & Technology-Hellas/FORTH), have submitted a proposal to the European Commission requesting funding for launching the conference series. The proposal was successful and the first conference was organized by FORTH in Crete, Greece in 1996 and the second one by University of Montpellier II at Montpellier, France in 1998. The present conference edition is co-organized by FORTH and the Electron Microscopy Laboratory (EML) of the Aristotle University of Thessaloniki (AUTH), which was also a partner of TECSICA. FORTH and AUTH are the main research organizations in Greece conducting SiC related research.

This collection of papers reflects the latest progress in the field of wide bandgap semiconductors, focusing on silicon carbide but also covering some selected aspects in related materials like silicon, graphene, gallium oxide and III-nitrides. We would like to thank all the contributors (both authors and reviewers) for their effort to warrant high scientific quality and timely publication of this Book of Proceedings. The present volume contains 176 contributions distributed among 7 topics: Bulk Growth, Epitaxial Growth, Material Properties and Characterization, Processing, Devices, Circuits and Applications, Related Materials. A novelty of these proceedings is that they are included (title, authors and abstract) in the Xplore database of the IEEE Society helping wider dissemination of papers published in this volume.

The conference would not have been successful without the labor of many people behind the main scene. The members of the Technical Program Committee organized an excellent technical program and accepted to organize parallel sessions for the first time in this conference while the members of the Organizing Committee have addressed successfully all issues related to the running of the conference. A special thanks is devoted to local people from FORTH (Heraklion), AUTH (Thessaloniki) and NTUC (Chania) for their help during the preparation and especially during the conference. The conference has been sponsored directly or in form of exhibition booth by more than 40 organizations and private companies. We would like to express our deepest appreciation to these partners.

The next conference of this series, will be held in Birmingham, UK in September 2018. We sincerely wish the organizers every success with ECSCRM 2018.

February 2017

Konstantinos Zekentes
Konstantin V. Vasilevskiy
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